Form PTO-1449 (modified)

List of Patents and Publications
For Applicant's Information

Disclosure Statement

(Use several sheets if necessary)

ATTY. DOCKET NO.	SERIAL NO.
MCRO:017-7/FLE	Unassigned

APPLICANT
Fernando Gonzalez et al.

FILING DATE	GROUP
Herewith	Unassigned

U.S. PATENT DOCUMENTS

EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
TL	A1	3,241,009	03/15/66	Dewald et al.	317	234	11/06/61
	A2	3,423,646	01/21/69	Cubert et al.	317	234	02/01/65
	A3	3,602,635	08/31/71	Romankiw	174	68.5	06/30/70
	A4	3,699,543	10/17/72	Neale	340	173R	12/22/69
	A5	3,796,926	03/12/74	Cole et al.	317	234 R	03/29/71
	A6	3,877,049	04/08/75	Buckley	357	2	11/28/73
	A7	3,886,577	05/27/75	Buckley	357	2	09/12/73
	A8	4,099,260	07/04/78	Lynes et al.	365	105	09/20/76
	A9	4,115,872	09/19/78	Bluhm	365	163	05/31/77
	A10	4,174,521	11/13/79	Neale	357	45	04/06/78
	A11	4,194,283	03/25/80	Hoffmann	29	571	08/16/78
	A12	4,227,297	10/14/80	Angerstein	29	571	07/31/78
	A13	4,203,123	05/13/80	Shanks	357	2	12/12/77
	A14	4,272,562	06/09/81	Wood	427	87	06/19/79
	A15	4,420,766	12/13/83	Kasten	357	59	02/09/81
	A16	4,433,342	02/21/84	Patel et al.	357	2	04/06/81
	A17	4,458,260	07/03/84	McIntyre et al.	357	30	11/20/81
	A18	4,499,557	02/12/85	Holmberg et al.	365	163	07/06/81
	A19	4,502,208	03/05/85	McPherson	29	584	08/26/83
	A20	4,502,914	03/05/85	Trumpp et al.	156	643	10/28/83
	A21	4,569,698	02/11/86	Feist	148	1.5	05/31/85
	A22	4,630,355	12/23/86	Johnson	29	575	03/08/85
	A23	4,641,420	02/10/87	Lee	29	511	08/30/84
	A24	4,642,140	02/10/87	Noufi et al.	148	6.24	04/30/85
TL	A25	4,666,252	05/19/87	Yaniv et al.	350	333	06/29/84

A26	4,677,742	07/07/87	Johnson	29	591	12/05/83
A27	4,757,359	07/12/88	Chiao et al.	357	23.5	04/07/86
A28	4,795,657	01/03/89	Formigoni et al.	427	96	04/08/85
A29	4,804,490	02/14/89	Pryor et al.	252	62.3 BT	10/13/87
A30	4,809,044	02/28/89	Pryor et al.	357	2	11/26/86
A31	4,823,181	04/18/89	Mohsen et al.	357	51	05/09/86
A32	4,876,220	10/24/89	Mohsen et al.	437	170	11/13/87
A33	4,876,668	10/24/89	Thakoor et al.	365	163	04/29/86
A34	4,881,114	11/14/89	Mohsen et al.	357	54	05/16/86
A35	4,892,840	01/09/90	Esquivel et al.	437	52	04/11/89
A36	5,144,404	09/01/92	Iranmanesh et al.	357	51	08/22/90
A37	5,166,096	11/24/92	Cote et al.	437	195	04/14/92
A38	5,166,758	11/24/92	Ovshinsky et al.	257	3	01/18/91
A39	5,177,567	01/05/93	Klersy et al.	257	4	07/19/91
A40	5,216,282	06/01/93	Cote et al.	257	773	10/29/91
A41	5,233,217	08/03/93	Dixit et al.	257	530	05/03/91
A42	5,293,335	03/08/94	Pernisz et al.	365	148	12/09/92
A43	5,296,716	03/22/94	Ovshinsky et al.	257	3	08/19/91
A44	5,310,693	05/10/94	Hsue	437	43	06/24/93
A45	5,335,219	08/02/94	Ovshinsky et al.	369	288	09/30/91
A46	5,341,328	08/23/94	Ovshinsky et al.	365	163	06/15/92
A47	5,359,205	10/25/94	Ovshinsky	257	3	05/08/92
A48	5,363,329	11/08/94	Troyan	365	184	11/10/93
A49	5,406,125	04/11/95	Johnson et al.	257	774	04/15/93
A50	5,414,271	05/09/95	Ovshinsky et al.	257	3	11/07/91
A51	5,429,988	07/04/95	Huang et al.	437	187	06/13/94
A52	5,510,629	04/23/96	Karpovich et al.	257	50	05/27/94
A53	5,534,711	07/09/96	Ovshinsky et al.	257	3	04/19/95
A54	5,534,712	07/09/96	Ovshinsky et al.	217	3	08/21/95
A55	5,536,947	07/16/96	Klersy et al.	257	3	07/25/95
A56	5,569,932	10/29/96	Shor et al.	257	3	01/23/95
A57	5,578,185	11/26/96	Bergeron et al.	205	123	01/31/95
A58	5,675,187	10/07/97	Numata et al.	257	758	05/16/96

FOREIGN PATENT DOCUMENTS

EXAM. INIT.	REF. DES.	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES/NO
TL	B1	1 319 388	06/06/73	Great Britain	H01L	9/00	Yes
TL	B2	0 117 045	08/29/84	EPA	H01L	45/00	Yes
TL	B3	JP 60109266	06/14/85	Japan	H01L	27/10	Yes

OTHER ART (Author, Title, Journal, Volume, Pertinent Pages, & Date)

TL	C1	Kim and Kim, "Effects of High-Current Pulses on Polycrystalline Silicon Diode with n-type Region Heavily Doped with Both Boron and Phosphorus," *J. Appl. Phys.*, 53(7):5359-5360, 1982.
	C2	Neale and Aseltine, "The Application of Amorphous Materials to Computer Memories," *IEEE*, 20(2):195-205, 1973.
	C3	Pein and Plummer, "Performance of the 3-D Sidewall Flash EPROM Cell," *IEEE*, 11-14, 1993.
	C4	Post and Ashburn, "Investigation of Boron Diffusion in Polysilicon and its Application to the Design of p-n-p Polysilicon Emitter Bipolar Transistors with Shallow Emitter Junctions," *IEEE*, 38(11):2442-2451, 1991.
	C5	Post et al., "Polysilicon Emitters for Bipolar Transistors: A Review and Re-Evaluation of Theory and Experiment," *IEEE*, 39(7):1717-1731, 1992.
	C6	Post and Ashburn, "The Use of an Interface Anneal to Control the Base Current and Emitter Resistance of p-n-p Polysilicon Emitter Bipolar Transistors," *IEEE*, 13(8):408-410, 1992.
	C7	Rose et al., "Amorphous Silicon Analogue Memory Devices," *J. Non-Crystalline Solids*, 115:168-170, 1989.
	C8	Schaber et al., "Laser Annealing Study of the Grain Size Effect in Polycrystalline Silicon Schottky Diodes," *J. Appl. Phys.*, 53(12):8827-8834, 1982.
	C9	Yamamoto et al., "The I-V Characteristics of Polycrystalline Silicon Diodes and the Energy Distribution of Traps in Grain Boundaries," *Electronics and Communications in Japan*, Part 2, 75(7):51-58, 1992.
	C10	Yeh et al., "Investigation of Thermal Coefficient for Polycrystalline Silicon Thermal Sensor Diode," *Jpn. J. Appl. Phys.*, 31(Part 1, No. 2A):151-155, 1992.
	C11	Oakley et al., "Pillars - The Way to Two Micron Pitch Multilevel Metallisation," *IEEE*, 23-29, 1984.
	C12	Prince, "Semiconductor Memories," A Handbook of Design, Manufacture, and Application, 2nd Ed., pgs. 118-123.

EXAMINER	DATE CONSIDERED
	7/4/04

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Information Disclosure Statement—PTO-1449 (Modified)

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